

AMENDMENTS TO THE SPECIFICATION:

Please replace the third full paragraph on page 16 with the following amended paragraph:

A specific example is next further described in detail. When fabricating a photomask, the correction table 4 is usually made before performing the OPC (optical proximity effect correction) processing 2, however the correction table 4 is written in correction grid units. Therefore, when developing a new process, a correction grid 3 must first be established. In this embodiment, the correction grid 3 is first set at 5 nm for example as the necessary value. In a correction grid 3 of 5 nm, by utilizing the space correction value (correction table 4) and the photomask 5 after those corrections, the line width after transferring (developing and processing) and etching of the wafer 6, is subtracted from the target line width (design line width) to achieve the value shown in FIG. 6. In FIG. 6, the curve I is the space correction value (correction table), curve II is the (ΔCD) differential between the line width after that transfer/processing and the target line width. Line width results depend on the five L/S (line/spaces) and the spaces are equal on both sides so it can be seen that a mask data will be 5 nm on one side and 10 nm on both sides.